



5SSA

Old part no. S 833

Silicon Surge Voltage Suppressor

Properties

- § Diffused pnp – Si structure
- § hermetically sealed in metal-ceramic package
- § Available to protect power devices (thyristors) against small and medium power surges (e.g. 200 kW over 10 μ s)

Applications

- § Traction, HVDC transmission, generator excitation,
- § transmitter power supply, high power motor controls

Mechanical Data

M_u	Mounting torque	10 ± 1 Nm
m	Weight	61 g
D_s	Surface creepage distance	15 mm
D_a	Air strike distance	15 mm

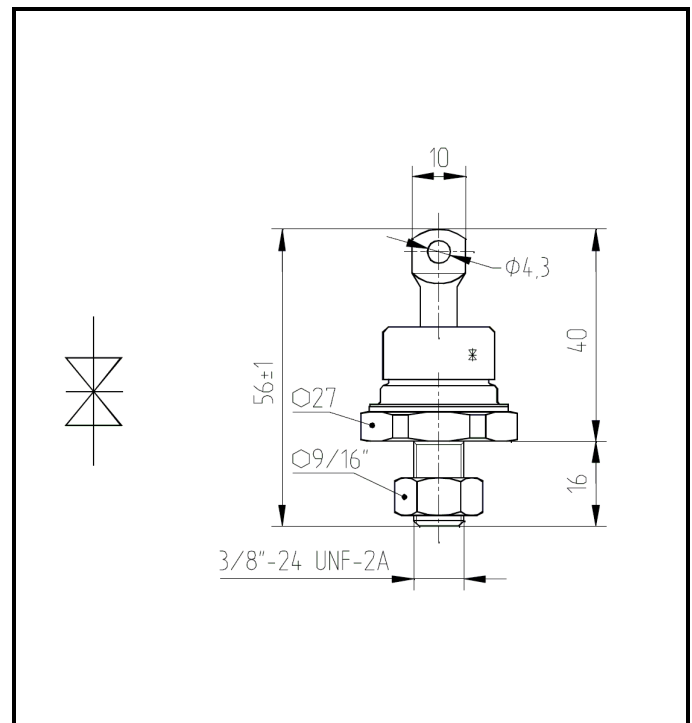


Fig. 1 Case



ABB s.r.o.

Novodvorska 1768/138a, 142 21 Praha 4, Czech Republic

tel.: +420 261 306 250, <http://www.abb.com/semiconductors>

type	Old part no.	V_R (V)	Thyristor V_{DRM} (V) V_{RRM} (V)	I_{RM} (A) for base width				P_{RAV} (W)
				$1 \times 10 \mu s$	$1 \times 100 \mu s$	$1 \times 1 ms$	$1 \times 10 ms$	
5SSA 50R0500	S 833-500-05	500 ± 60	500	500	135	33	7.5	30
5SSA 50R0600	S 833-500-06	600 ± 60	600					
5SSA 38R0700	S 833-380-07	700 ± 60	700	380	100	25	4.5	
5SSA 38R0800	S 833-380-08	800 ± 60	800					
5SSA 30R0900	S 833-300-09	900 ± 60	900	300	80	21	4.0	
5SSA 30R1000	S 833-300-10	1000 ± 60	1000					
5SSA 26R1100	S 833-260-11	1100 ± 60	1100	260	67	18	3.6	
5SSA 26R1200	S 833-260-12	1200 ± 60	1200					
5SSA 23R1300	S 833-230-13	1300 ± 60	1300	230	58	15	3.4	
5SSA 23R1400	S 833-230-14	1400 ± 60	1400					
5SSA 20R1500	S 833-200-15	1500 ± 60	1500	200	50	13	3.0	
5SSA 20R1600	S 833-200-16	1600 ± 60	1600					

Notes:

V_R ... Symmetrical avalanche voltage at $I_A = 20 A$, $t_p = 10 \mu s$, $T_{vj} = 60 \text{ }^\circ\text{C}$

I_{RM} ... Max. avalanche current for a single sine half wave pulse

P_{RAV} ... Admissible continuous losses at $R_{thja} < 1 K/W$, $T_a < 60 \text{ }^\circ\text{C}$

T_{vj} ... the initial virtual junction temperature

Maximum Ratings		Maximum Limits	Unit
$T_{jmin} - T_{jmax}$	Operating temperature range	-40 ÷ 125	°C
T_{STG}	Storage temperature range	-40 ÷ 125	°C
	Admissible acceleration (vibration)	10	m/s ²

Characteristics		Value		Unit
		<i>typ</i>	<i>max</i>	
V_R	Dependence of avalanche voltage V_R on junction temperature <i>Note 1</i>	$V_R(T) = V_{RO}[1 + 1.1 \times 10^{-3}(T - 60 \text{ °C})]$		V
C_j	Junction capacitance $V_R = 0 \text{ V}, T_j = 60 \text{ °C}$	1 100		pF
R_{thjh}	Thermal resistance junction to heatsink <i>Note 2</i>		0.6	K/W

Note 1: $V_R(60\text{°C}) = V_{RO}$; $V_R(25\text{°C}) = 0,96 \times V_{RO}$; $V_R(125\text{°C}) = 1,07 \times V_{RO}$

Notes: